Soft X-ray Resonant Magnetic Scattering Studies on Fe/CoO Exchange Bias System

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We have used soft X-ray Resonant Magnetic Scattering (XRMS) to search for the presence of an effective ferromagnetic moment belonging to the antiferromagnetic (AF) layer which is in close contact with a ferromagnetic (F) layer. Taking advantage of the element specificity of the XRMS technique, we have measured hysteresis loops of both Fe and CoO layers of a CoO (40 A)/Fe(150 A) exchange bias bilayer. From these measurements we have concluded that the proximity of the F layer induces a magnetic moment in the AF layer. The F moment of the AF layer has two components: one is frozen and does not follow the applied magnetic field and the other one follows in phase the ferromagnetic magnetization of the F layer. The temperature dependence of the F components belonging to the AF layer is shown and discussed.

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I. INTRODUCTION

Exchange bias refers to a shift of the ferromagnetic (F) hysteresis loop to positive or negative values when a F system is in contact with an antiferromagnetic (AF) system and cooled in an applied magnetic field through the Neel temperature of the AF system. The exchange bias phenomenon is associated with the interfacial exchange coupling between ferromagnetic and antiferromagnetic spin structures, resulting in a unidirectional magnetic anisotropy [1]. While the unidirectional anisotropy was successfully introduced by Meiklejohn and Bean (M&B), the origin of the enhanced coercive field is yet not well understood. The exchange bias effect is essential for the development of magneto-electronic switching devices (spin-valves) and for random access magnetic storage units. For these applications a predictable, robust, and tunable exchange bias effect is required.

Extensive data have been collected on the exchange bias field H_{EB} and the coercivity field H_c, for a large number of bilayer systems, which are reviewed in Ref. [2, 3, 4, 5]. The details of the EB effect depend crucially on the AF/F combination chosen and on the structure and thickness of the films. However, some characteristic features apply to most systems: (1) H_{EB} and H_c increase as the system is cooled in an applied magnetic field below the blocking temperature T_B T_N of the AF layer, where T_N is the Neel temperature of the AF layer; (2) the magnetization reversal can be different for the ascending and descending part of the hysteresis loop [6, 7, 8, 9], as was first pointed out in reference [10]; (3) thermal relaxation effects of H_{EB} and H_c indicate that a stable magnetic state is reached only at very low temperatures [11, 12, 13].

Several theoretical models have been developed for describing possible mechanisms of the EB effect, including domain formation in the AF layer with domain walls perpendicular to the AF/F interface [14], creation of uncompensated excess AF spins at the interface [15], or the formation of domain walls in the AF layer parallel to the interface [16, 17]. Another approach is the consideration of diluted antiferromagnets in an exchange field. In the work of Miltenyi et al., Keller et al., and Nowak et al.[18, 19, 20] the discussion about compensated versus uncompensated interfacial spins is replaced by a discussion of net magnetic moments within the antiferromagnetic layer. The AF domains will carry a resulting magnetization which will decrease non-exponentially with very high relaxation times. This induced magnetization in the AF layer is frozen and within the Domain State model it is responsible for the hysteresis shift. Ohldag et al. [21] and Kappenberger et al. [22] observed that a small fraction of the AF spins are uncompensated and responsible for the EB shift, as predicted by M&B model [1]. We concentrate on the observation of rotatable AF spins which contribute to the enhanced coercivity, reported for almost all system described in the literature. They are essential for understanding the coercivity enhancement as shown in Ref. [23]. There, the coercivity was modelled by an extended M&B model and assuming an interface AF layer with variably anisotropy.

In this paper, hysteresis loops of the induced ferromagnetic components belonging to the AF layer at the AF/F are described and compared with the magnetization curves of the ferromagnet itself.

II. SAMPLE GROWTH AND HARD X-RAY CHARACTERIZATION

As substrate we used epi-polished single-crystalline (1120)-oriented sapphire wafer. Before deposition, the substrates were ultrasonically cleaned in acetone and ethanol and then transferred into a high-vacuum rf-sputtering chamber which provides a base pressure of 1 10^7 mbar. Prior to the deposition the substrate were annealed at 500 C for 3 h and etched for 10 min with an Ar ion beam. Then the substrate was cooled down to 200 C, where the Fe layer has been deposited by rf-sputtering in Ar with a partial pressure of 5 10^3 mbar. Subsequently, the polycrystalline CoO layer has been grown by sputtering of Co atoms in a mixture of Ar (94%) and O_2 (6%). The deposition rates were 0.48 A/s

and 0.57 A/s for Fe and CoO, respectively. The expected nominal thicknesses, as calculated from deposition rates, were 150 A and 40 A for Fe and CoO, respectively. After deposition, the structural quality of the bilayers was probed by x-ray diraction and reectivity, which is described further below.

X-ray scattering is most suitable for detailed structural characterization of thin lms and heterostructures. Information about the electron density prole perpendicular to the lm plane is obtained via reectivity measurements. High-angle radial scans at a reciprocal-lattice point (Bragg scans) provide information about the crystalline properties of the lms. The hard x-ray measurements were carried out with the use of synchrotron radiation at the W 1.1 beam line at HASYLAB. The radiation wavelength was = 1.5408 A.

Fig. 1a shows a reectivity curve of the CoO/Fe bilayer structure deposited on a Al_2O_3(1120) substrate. The thickness oscillations corresponding to the Fe layer are clearly visible up to Q = 0.6 A ^{1} with a small amplitude modulations corresponding to the CoO layer, where Q is the scattering vector Q = (4 =)sin . A t of this reectivity curve using the Parratt formalism [24] and the roughness model of Nevot and Croce [25] gives the electron density prole presented in the inset in Fig. 1a.

Fig. 1b shows the radial scan in the direction normal to the diraction planes, around the Al_2O_3(1120) and Fe(110) Bragg peak positions. The Laue oscillations on either sides of the main Fe(110) Bragg peak are clearly seen. They reveal both a good crystalline quality of the iron layer and an high interface quality between the Fe and CoO layer. The smaller intensity of Al_2O_3(1120) substrate peak results from a small and intentional misalignment. We have not found any Bragg reections from the CoO layer. Therefore we concluded that this layer is polycrystalline. The deposition temperature of the CoO was 200 C, which is the optimal growth temperature for polycrystalline CoO, obtained from detailed growth studies presented in Ref. [26]. The crystalline quality of cobalt oxide was intentionally sacrced in order to achieve a smooth CoO/Fe interface, and to eliminate orientational diculties, characteristic for mono-crystalline CoO layers.

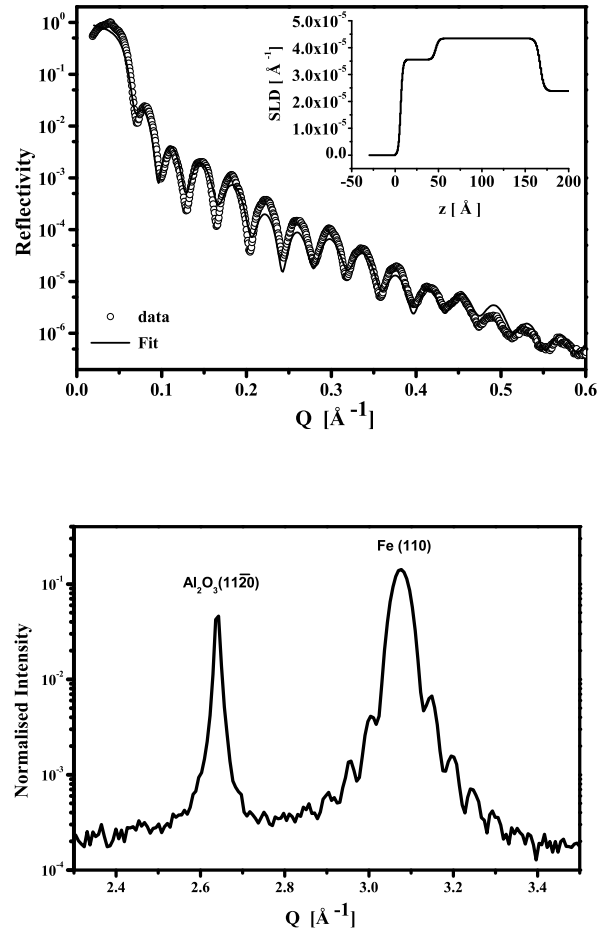

FIG. 1: a) Reectivity curve of the CoO/Fe bilayer structure (symbols – the experimental data, line – the t using a model presented in the inset). b) The radial scan in the direction normal to the sample surface around the Al_2O_3(1120) and Fe(110) Bragg peak positions.

III. SOFT X-RAY RESONANT MAGNETIC SCATTERING STUDIES

X-ray resonant magnetic scattering (XRMS) provides direct information on the magnetic structure of materials. In order to study XRMS of 3d transition metals, the L absorption edges must be utilized, which are located in the soft x-ray range. Soft x-ray resonant magnetic scattering using either circularly or linearly polarized x-rays, has proven to be a highly useful technique for the study of magnetic properties of buried layers, interfaces and, depth-dependent magnetic properties. Moreover, by varying the external magnetic eld applied parallel to the sample plane and parallel to the x-ray circular helicity, close to energies corresponding to L absorption edges element-specic hysteresis loops can be measured [27]. The XRMS experiments were carried out at the undulator beam lines UE 56/1& 2 and bending magnet beam-line PM 3 of BESSY. Since for this energy range special vacuum conditions are required, a UHV-diractometer ALICE [28] was used for the experiments to be described below. The magnetic eld was applied in the scattering plane and parallel to the sample surface.

A. Reectivity and asymmetry ratio

Fig. 2 shows the reectivities of CoO/Fe bilayer measured at room temperature for the magnetic eld applied

in the sample plane parallel (I^+) and antiparallel (I^-) to the photon helicity. The photon energy of the circular polarized light was tuned close to the L_3 absorption edge of Co (Fig. 2a) and Fe (Fig. 2b), respectively. The highest magnetic sensitivity is reached at the maxima of the thickness oscillations. The energy dependence of the asymmetry ratio $A = (I^+ - I^-)/(I^+ + I^-)$ is depicted in Fig. 3 for a fixed scattering angle of $2\theta = 32^\circ$. Strikingly, the asymmetry of Co does not vanishes as expected for AF materials. Moreover, even above the Neel temperature ($T_N = 291$ K) a ferromagnetic signal belonging to the CoO layer is still visible.

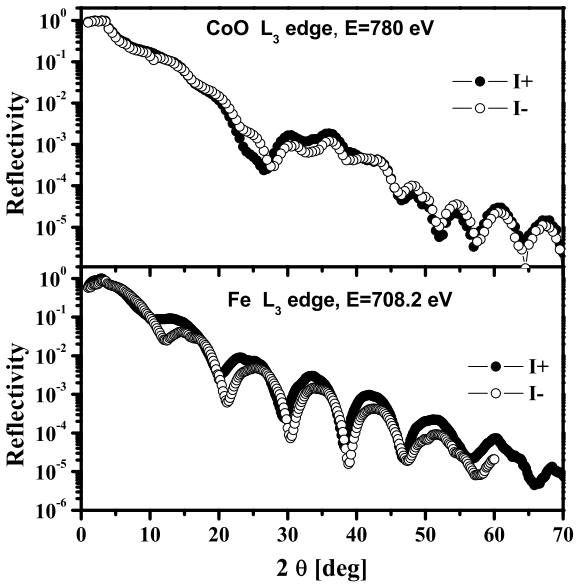

FIG. 2: The reflectivities of CoO/Fe bilayer measured at room temperature for the magnetic field applied in the sample plane parallel (I^+, closed symbols) and antiparallel (I^-, open symbols) to the photon helicity. The energy of the circular polarized light was tuned close to the L_3 absorption edges of Co (a) and Fe (b), respectively.

The reflectivities shown in Fig. 2 reveal the sign of the interfacial coupling of the two ferromagnetic materials in question, which share a common interface or which are exchange coupled over a nonmagnetic layer. For both layers the minima in the I^+ reflectivity curve always lies at lower angles than the minima in the I^- curves. This allows to clearly conclude that the magnetization of both layers is parallel. An antiparallel alignment of the layer would produce a reverse position of the minima in the reflectivity curves. It should be pointed out that element-specific anti-phase hysteresis loops is not characteristic for the coupling sign [29]. This can be seen from the reflectivity curves. At some incident angles the asymmetry is positive for Fe and negative for CoO. Therefore, taken the hysteresis loops alone they would suggest an

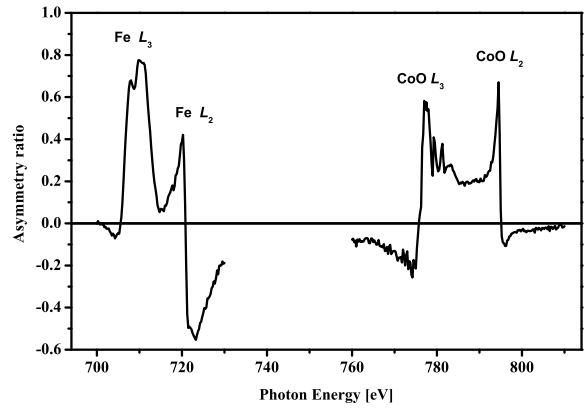

FIG. 3: The energy dependence of the asymmetry ratio for a fixed scattering angle of $2\theta = 32^\circ$.

AF-coupling between the layers, whereas the true orientation is ferromagnetic, as clearly seen in the reflectivity curves.

B. Temperature dependence of the element-specific hysteresis loops

The exchange bias hysteresis loops measured at the L_3 absorption edges of Co (E = 780 eV, closed symbols) and Fe (E = 708.2 eV, open symbols) and for different temperatures are shown in Fig. 4. The measuring procedure is as follows: first the system was heated up to T = 300 K, which is well above the Neel temperature of CoO. Here, a field of +2000 Oe was applied parallel to the sample plane and parallel to the helicity of the circular polarization of the x-ray beam. Subsequently, the system was field cooled to the lowest available temperature, which is about 30 K. Here, several hysteresis loops were measured (not shown) in order to eliminate training effects of the hysteresis loops. After acquiring a stable reversible magnetization curve at 30 K, we raised the temperature stepwise, from low to high T, and for each temperature we measured one element-specific hysteresis loop at the energies corresponding to Fe and CoO, respectively. The hysteresis loops of Fe as a function of temperature show a typical behavior. At low temperatures an increased coercive field and a shift of the hysteresis loop is observed. As the temperature is increased, the coercive field and the exchange bias decrease until the blocking temperature is reached. Here, the exchange bias vanishes and the coercive field shows little changes as the temperature is further increased. Strikingly, a ferromagnetic hysteresis loop corresponding to the CoO layer is observed for all temperatures, following closely the hysteresis loop of Fe (or vice versa), with some notable differences. It appears that the ferromagnetic components of CoO develop

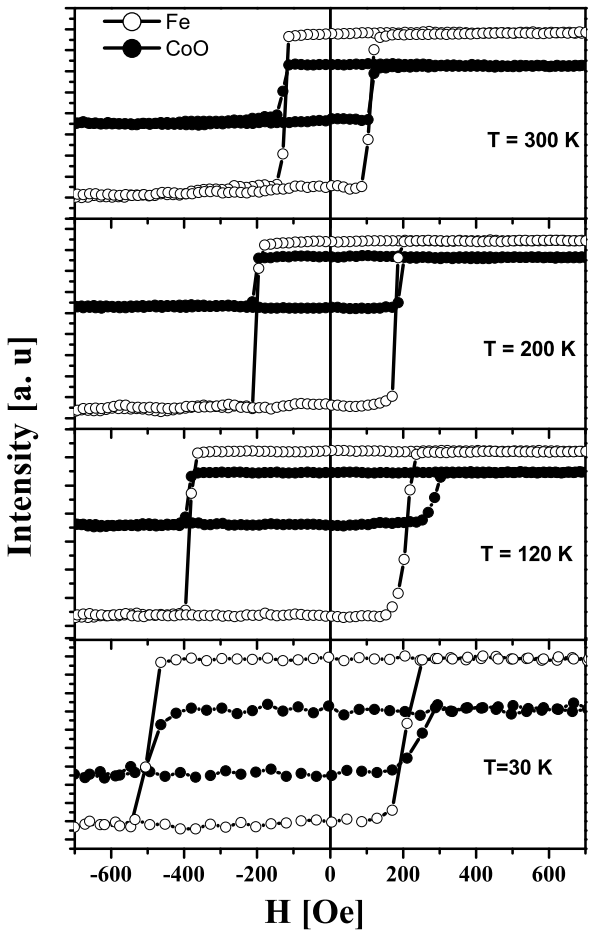

FIG. 4: The temperature dependence of the exchange bias hysteresis loops measured at L_3 absorption edges of Co (E = 780 eV, closed symbols) and Fe (E = 708.2 eV, open symbols). Scattering angle is 2 = 32 .

different coercive fields than Fe below the blocking temperature. Moreover, the ferromagnetic moment of CoO is present also above the Neel temperature. Here, the AF layer is in a paramagnetic state, therefore the magnetic moment per spin is very low for applied fields used here. It implies, that a ferromagnetic layer should be present at the interface between Fe and CoO with a Curie temperature, higher then the Neel temperature of CoO.

C. XRMS comparison between CoO single layer and CoO/Fe bilayer system

In order to exclude the presence of Co clusters in the CoO layer as a possible explanations of our results presented above, we have prepared two additional samples with the same sputtering technique: one was the same CoO/Fe exchange bias system and another one grown in the same run was just a simple CoO layer deposited on a sapphire substrate. First both samples were field cooled and then we measured at low temperatures the element specific hysteresis loops at the L_3 absorption edge of Co. For the CoO/Fe bilayer the previous results were reproduced. But for the single CoO layer no ferromagnetic signal was observed. We infer from this the absence of cobalt clusters in the CoO layer [30]. Vice versa, the ferromagnetic moment in the CoO layer must be induced by the proximity between the F and the AF layer. The induced magnetic moment appears to consist of two parts. One part of the spins are strongly coupled to the AF itself. They do not rotate with the rotation of the F layer. Another part of these spins have a reduced AF anisotropy and due to exchange coupling to the F layer, they show a similar hysteresis loop as the F layer.

IV. DISCUSSION

The M&B model [1] assumes that the AF spins rigidly form an AF state, but they may slightly rotate as a whole during the magnetization reversal of the F layer. Within the M&B model, enhanced coercivity is not accounted for. The interface is assumed to be perfectly uncompensated with the interface AF spins having the same anisotropy as the bulk spins. However, the interface is never perfect. Roughness, deviations from stoichiometry, interdiffusion, structural defects, etc. cause non-ideal magnetic interfaces. It is therefore naturally to assume that, statistically, a fraction of the AF spins have lower anisotropy as compared to the bulk ones. These interfacial AF spins can rotate together with the ferromagnet. They mediate the exchange coupling, induce an enhanced coercivity, but soften the extreme coupling condition assumed by M&B. Therefore, we assume that the anisotropy of the AF interface layer varies from $K_{int} = 0$ next to the F layer to $K_{int} = K_{AF}$ next to the AF layer, where K_{AF} is the anisotropy constant of a presumably uniaxial antiferromagnet. This variation of the anisotropy constant across the interface governs the enhanced anisotropy of the ferromagnetic layer. So far it was believed that the enhanced coercivity in F/AF exchange biased systems is caused by compensated AF spins at the F/AF interface. We argue that for most of the AF materials a compensated or uncompensated spin having the same anisotropy as the bulk AF layer would be practically impossible to reverse by rotating the F layer. Therefore we need to assume low anisotropy AF spins in order to qualitatively describe the rotating AF seen in the experimental data. Evidence for the existence of low anisotropy AF spins at the F/AF interface is provided here through measurements of element specific hysteresis loops.

V. CONCLUSIONS

We have investigated the ferromagnetic behavior of the AF spins for an Fe/CoO exchange bias bilayer. For all temperatures we observe a non-vanishing ferromagnetic hysteresis loop of the spins belonging to the AF layer. They reverse, in phase, with the spins of the Fe layer, but display a different coercive field. We assume that those AF spins are located at the interface between the F/AF layer, and that they have, on average, a reduced AF anisotropy. This assumption may lead to a better understanding of the enhanced coercivity observed in almost all F/AF systems.

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